



## Product Summary

- $V_{DS} = -30V, I_D = -8A$
- $R_{DS(ON)} = 18m\Omega @ -10V$
- $R_{DS(ON)} = 20m\Omega @ -4.5V$

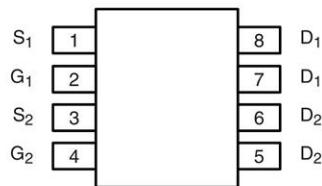
## Application

- DC-DC Converters.
- Load Switch.
- Power Management.

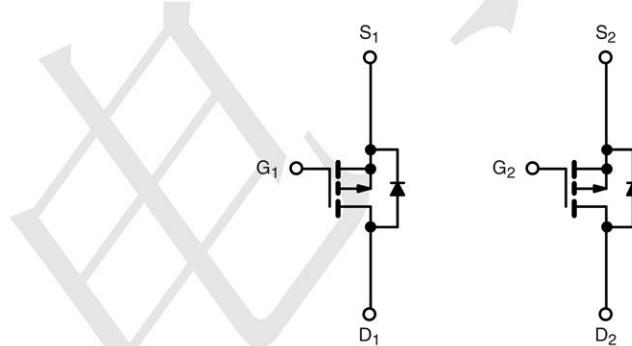
## Package and Pin Configuration



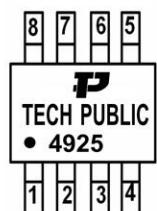
SOP-8 top view



## Circuit diagram



## Marking:



## Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current	$I_D^{(1)}$	-8	A
Pulsed Drain Current	$I_{DM}^{(2)}$	-32	
Power Dissipation	$P_D^{(5)}$	3.0	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}^{(5)}$	41.6	$^\circ C/W$
Operating Junction and Storage Temperature	$T_J, T_{stg}$	-55 ~ +150	$^\circ C$



**Electrical Characteristics (  $T_A = 25^\circ\text{C}$  unless otherwise noted )**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Off characteristics</b>						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = -250\mu\text{A}$	-30			V
Zero gate voltage drain current	$I_{\text{DSS}}$	$V_{\text{DS}} = -24\text{V}, T_J = 25^\circ\text{C}$			-15	$\mu\text{A}$
		$V_{\text{GS}} = 0\text{V}, T_J = 125^\circ\text{C}$			-100	
Gate-body leakage current	$I_{\text{GSS}}$	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 20\text{V}$			$\pm 100$	nA
<b>On characteristics</b> <sup>(3)</sup>						
Gate-threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = -250\mu\text{A}$	-1.0	-1.6	-2.5	V
Static drain-source on-state resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = -10\text{V}, I_D = -8\text{A}$		18	25	$\text{m}\Omega$
		$V_{\text{GS}} = -4.5\text{V}, I_D = -4.5\text{A}$		20	35	$\text{m}\Omega$
Forward transconductance	$g_{\text{fs}}$	$V_{\text{DS}} = -10\text{V}, I_D = -8\text{A}$		16		S
<b>Dynamic characteristics</b> <sup>(3)(4)</sup>						
Input capacitance	$C_{\text{iss}}$	$V_{\text{DS}} = -15\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		1650		pF
Output capacitance	$C_{\text{oss}}$			345		
Reverse transfer capacitance	$C_{\text{rss}}$			285		
<b>Switching characteristics</b> <sup>(3)(4)</sup>						
Total gate charge	$Q_g$	$V_{\text{GS}} = -10\text{V}, V_{\text{DS}} = -15\text{V}, I_D = -8\text{A}$		39		nC
Gate-source charge	$Q_{\text{gs}}$			9.8		
Gate-drain charge	$Q_{\text{gd}}$			8.3		
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = -15\text{V}, I_D = -1\text{A}, V_{\text{GS}} = -10\text{V}, R_G = 6\Omega, R_D = 15\Omega$		12		ns
Turn-on rise time	$t_r$			16		
Turn-off delay time	$t_{\text{d}(\text{off})}$			125		
Turn-off fall time	$t_f$			72		
<b>Drain-Source Diode Characteristics</b>						
Drain-source diode forward voltage	$V_{\text{SD}}$ <sup>(3)</sup>	$V_{\text{GS}} = 0\text{V}, I_S = -2\text{A}$			-1.2	V
Continuous drain-source diode forward current	$I_S$ <sup>(1)</sup>				-8	A
Pulsed drain-source diode forward current	$I_{\text{SM}}$ <sup>(2)</sup>				-32	A



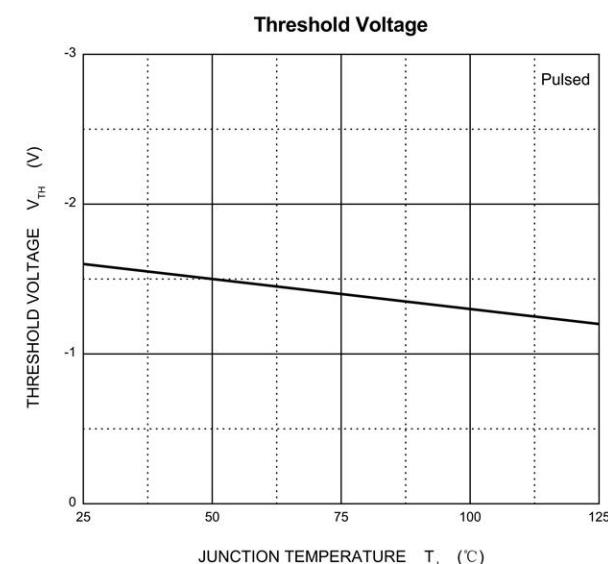
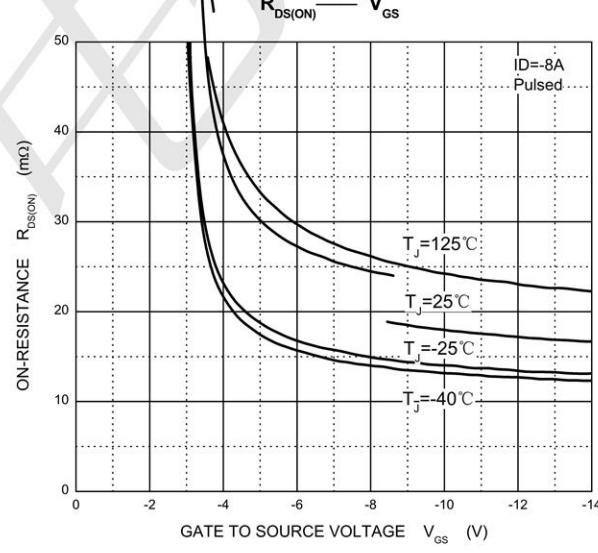
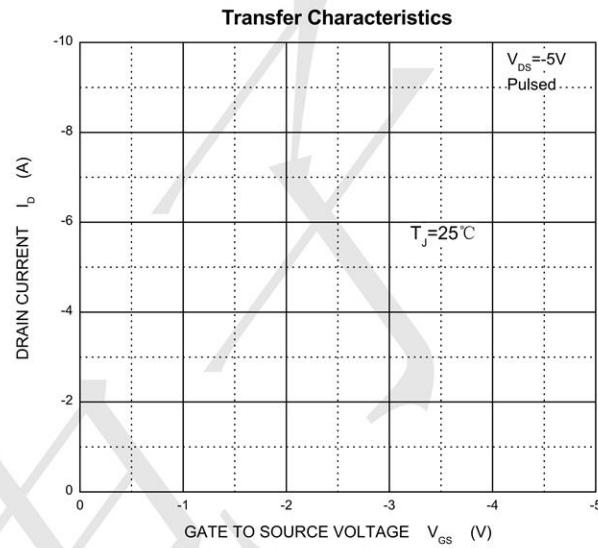
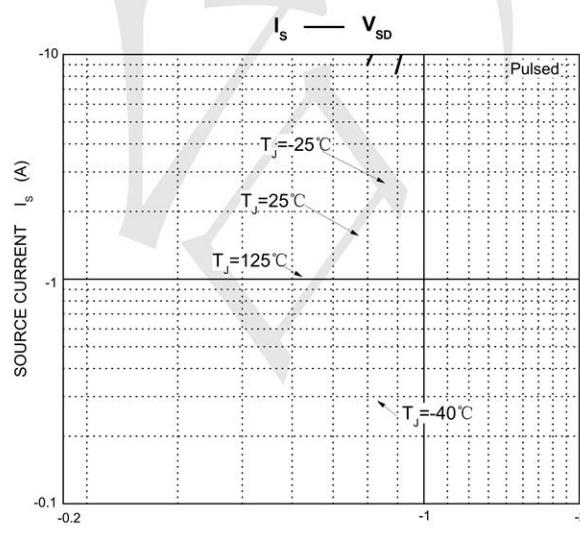
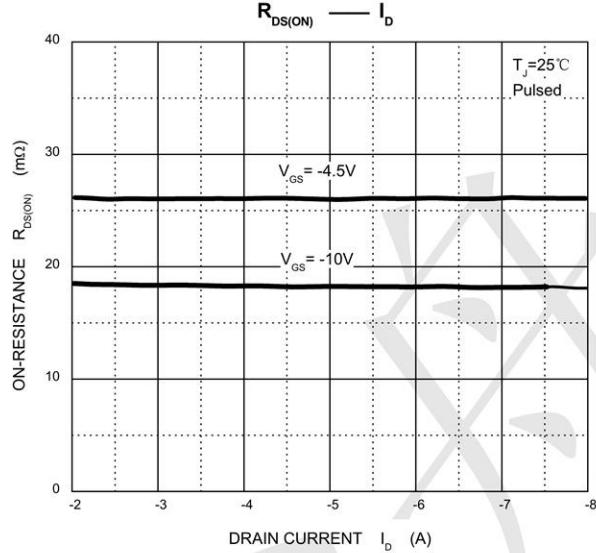
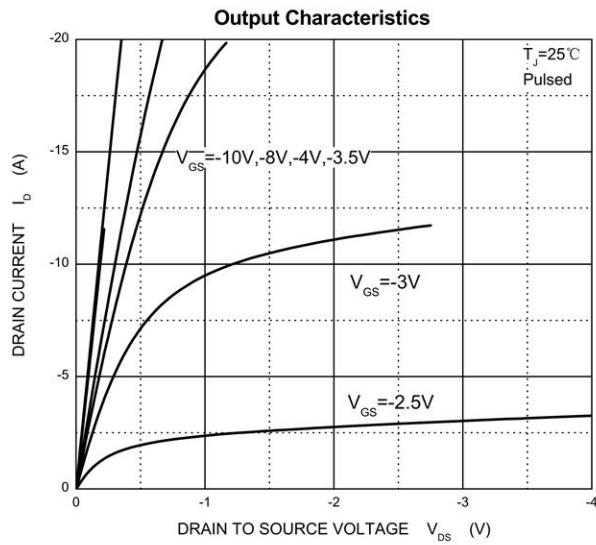
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**SI4925DDY**

Dual P-Channel MOSFET

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**Typical Performance Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise Specified)**





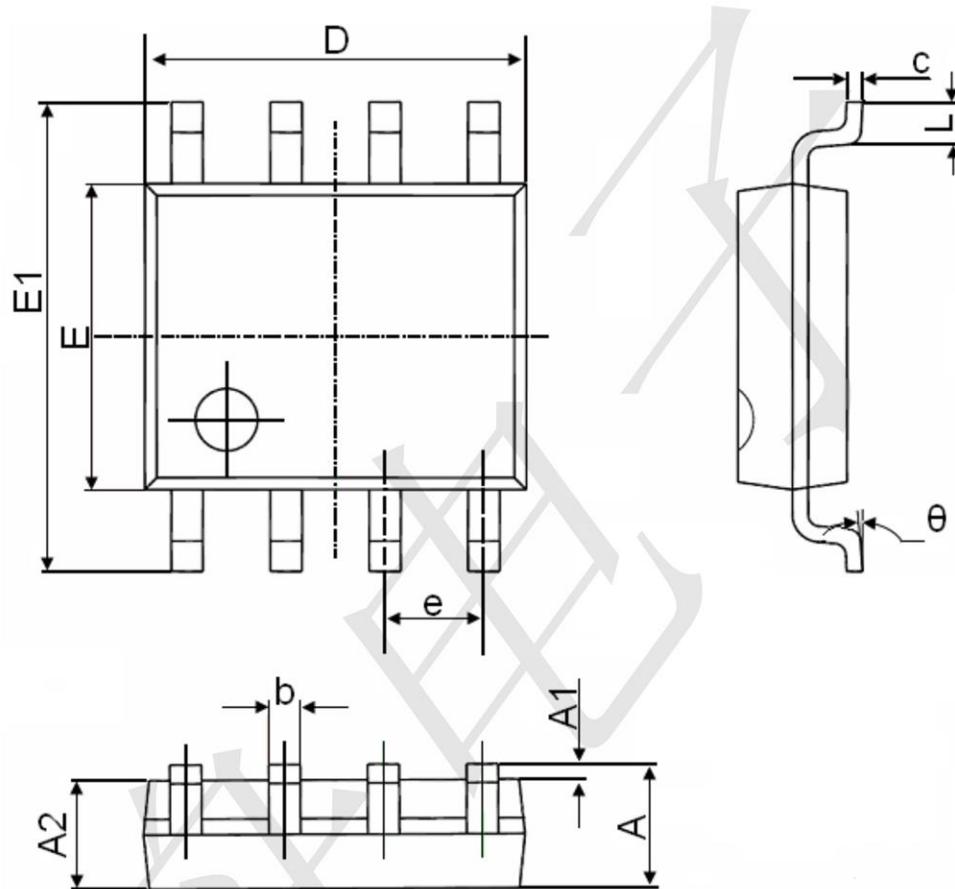
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### SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°